

ABSTRACT

5

**Fault Tolerant Magnetoresistive
Solid-state Storage Device**

A magnetoresistive solid-state storage device (MRAM)
10 performs error correction coding (ECC) of stored
information. At manufacture or during use, each logical
block of ECC encoded data and/or the corresponding set of
storage cells are evaluated to determine suitability for
continued use, or whether remedial action is necessary.
15 In a first preferred method ECC decoding is attempted to
determine whether information is unrecoverable from the
block of ECC encoded data. In a second preferred method a
parametric evaluation is made prior to attempting ECC
decoding.

20

[Figure 3]